

Section 101

5 A flip chip type semiconductor device comprises at least one first
metal line and at least a pair of second metal lines formed in the passivation
layer, an aluminum pad covering the first metal line, an aluminum fuse
covering the pair of second metal lines adjacent to each other and the
passivation layer therebetween, and an under-bump metal layer pattern and a
bump formed on the aluminum pad in order. The first and second metal lines
are formed respectively in first and second grooves by using a damascene
process after forming first and second grooves in the passivation layer.

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